

MMBTA05 / MMBTA06 / MMBTA55 / MMBTA56

NPN AND PNP HIGH VOLTAGE TRANSISTOR

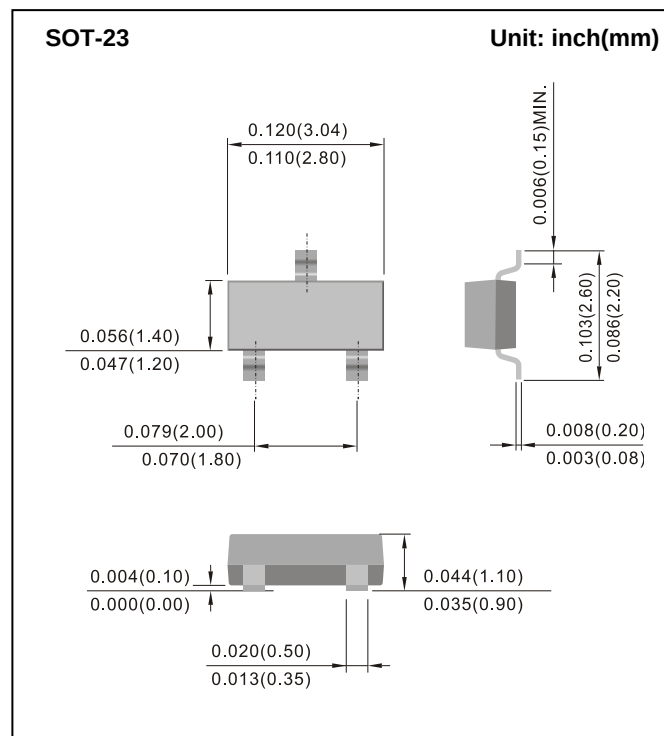
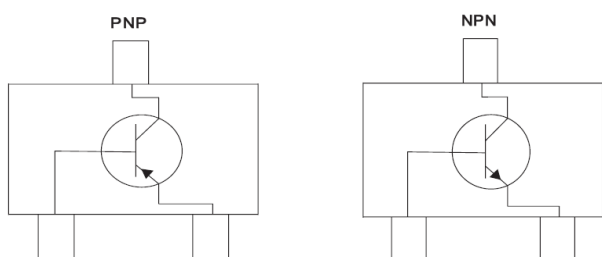
Voltage	60~80V	Power	225mW
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Features

- NPN and PNP silicon, planar design
- Collector current $I_C = 500\text{mA}$
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: SOT-23 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	MMBTA05	MMBTA55	MMBTA06	MMBTA56	UNITS
Marking		B05	B55	B06	B56	
Collector-Emitter Voltage	V _{CEO}	60		80		V
Collector-Base Voltage	V _{CBO}	60		80		V
Emitter-Base Voltage	V _{EBO}	4				V
Collector Current-Continuous	I _C	500				mA
Circuit Figure		NPN	PNP	NPN	PNP	

Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

CHARACTERISTIC	SYMBOL	MAX.	UNITS
Total device dissipation FR-4 board (Note 1) $T_A=25^\circ\text{C}$	P_D	225	mW
derate above 25°C		1.8	mW/ $^\circ\text{C}$
Typical thermal resistance	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total device dissipation alumina substrate (Note 2) $T_A=25^\circ\text{C}$	P_D	300	mW
derate above 25°C		2.4	mW/ $^\circ\text{C}$
Typical thermal resistance	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

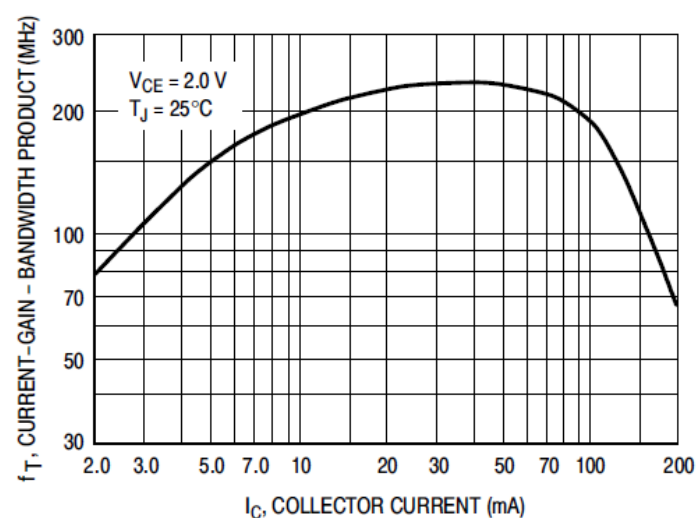
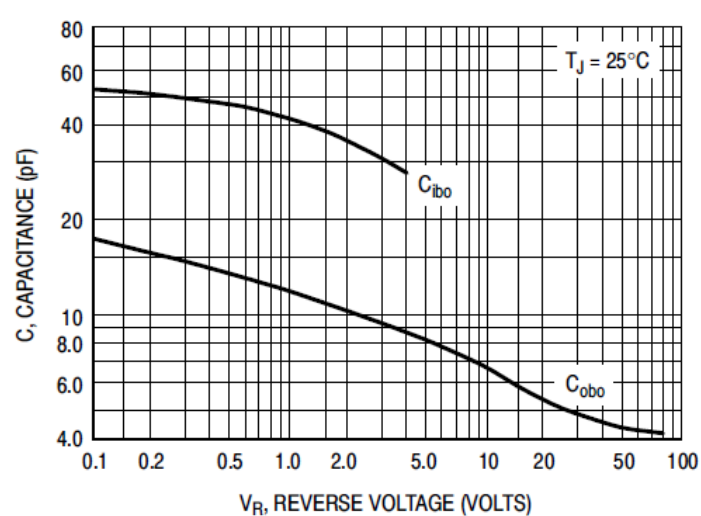
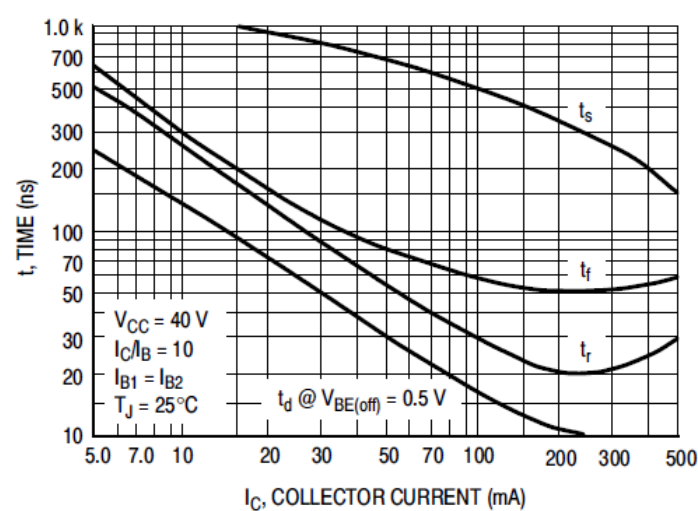
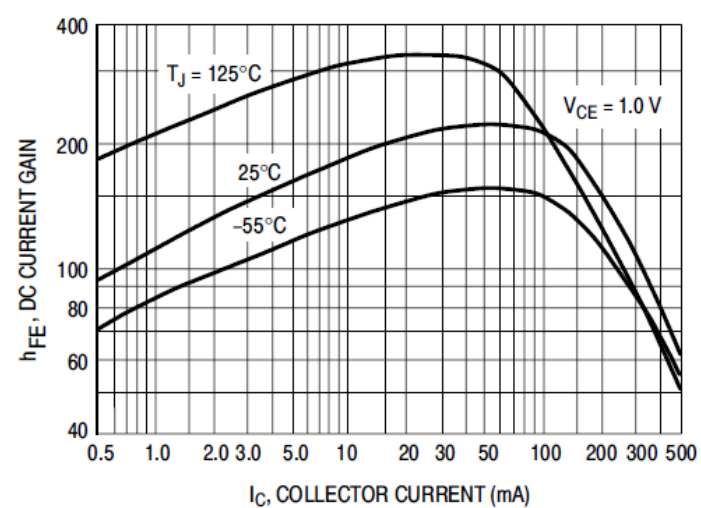
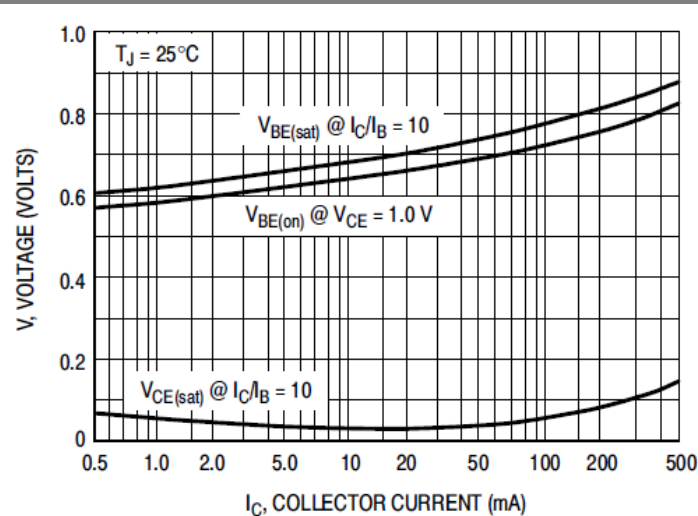
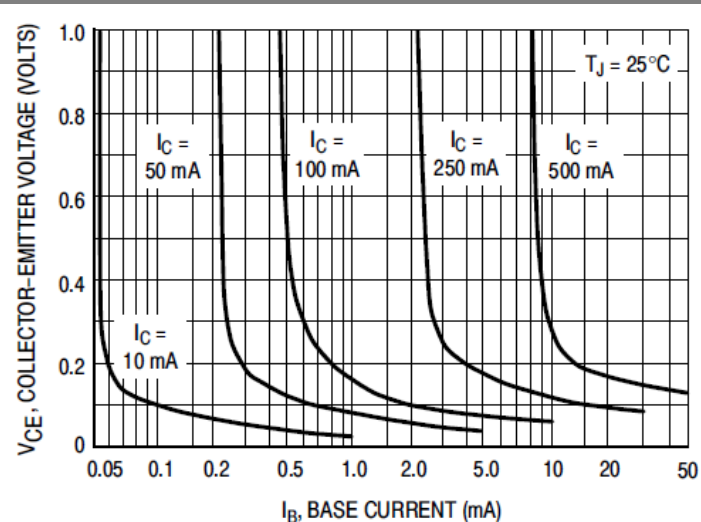
Note : 1. FR-4=70 x 60 x 1mm.

2. Alumina=0.4 x 0.3 x 0.024 in. 99.5 alumina.

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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	MIN.	MAX.	UNITS
OFF Characteristics				
Collector-Emitter Breakdown Voltage (I _C =1.0mA, I _B =0)	V _{(BR)CEO}	60	-	V
MMBTA05, MMBTA55 MMBAT06, MMBTA56		80	-	
Emitter-Base Breakdown Voltage (I _E =100μA, I _C =0)	V _{(BR)EBO}	4	-	V
Collector Cutoff Current (V _{CE} =60V, I _B =0)	I _{CES}	-	0.1	μA
Collector Cutoff Current (V _{CB} =60V, I _E =0)	I _{CBO}	-	0.1	μA
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ON characteristics				
DC Current Gain (I _C =10mA, V _{CE} =1V)	f _{FE}	100	-	-
(I _C =100mA, V _{CE} =1V)		100	-	
Collector-Emitter Saturation Voltage (I _C =100mA, I _B =10mA)	V _{CE(SAT)}	-	0.25	V
Base-Emitter On Voltage (I _C =100mA, V _{CE} =1V)	V _{BE(ON)}	-	1.2	V
Small-signal characteristics				
Current-Gain-Bandwidth Product (I _C =10mA, V _{CE} =2V, f=100MHz)	f _T	100	-	MHz

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Fig.1 Current-Gain—Bandwidth Product

Fig.2 Capacitance

Fig.3 Switching Time

Fig.4 DC Current Gain

Fig.5 ON Voltages

Fig.6 Collector Saturation Region

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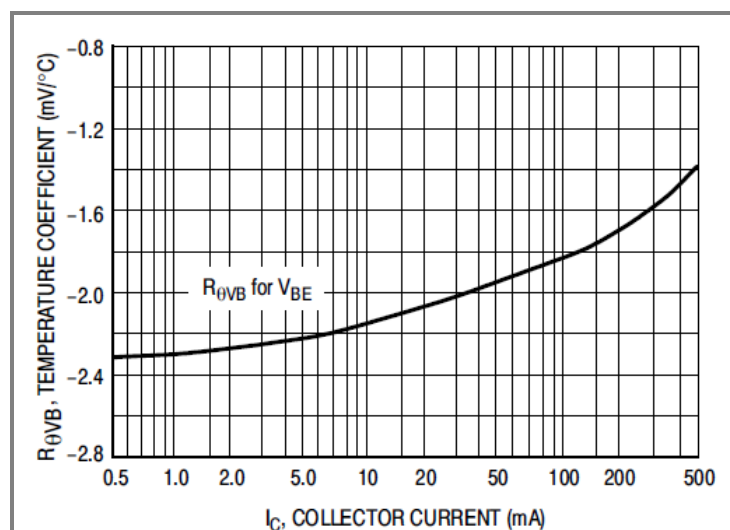


Fig.7 Base-Emitter Temperature Coefficient

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Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
MMBTA05_R1_00001	SOT-23	3K / 7" Reel	B05	Halogen Free
MMBTA05_R2_00001	SOT-23	12K / 13" Reel	B05	Halogen Free

Mounting Pad Layout

